

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	34	C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.3	0.75	1.2	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance		$V_{GS} = 4.5V, I_D = 6.5A$				
		$V_{GS} = 2.5V, I_D = 5A$				
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 5A$				
Source-drain voltage	V_{SD}	$I_S = 5.0A$				

Electronic Characteristics

Parameter	Symbol	Condition
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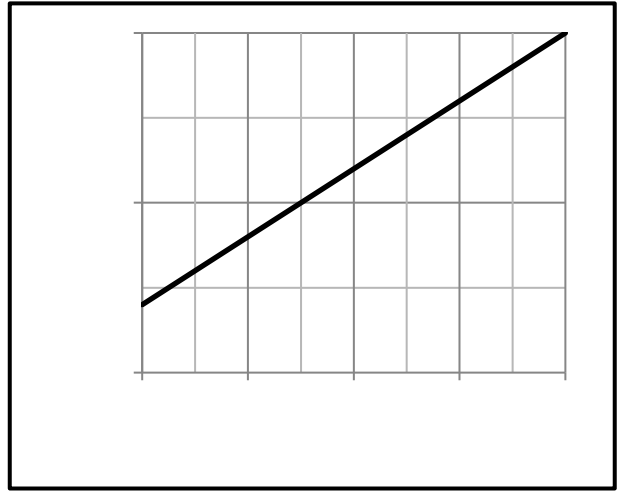
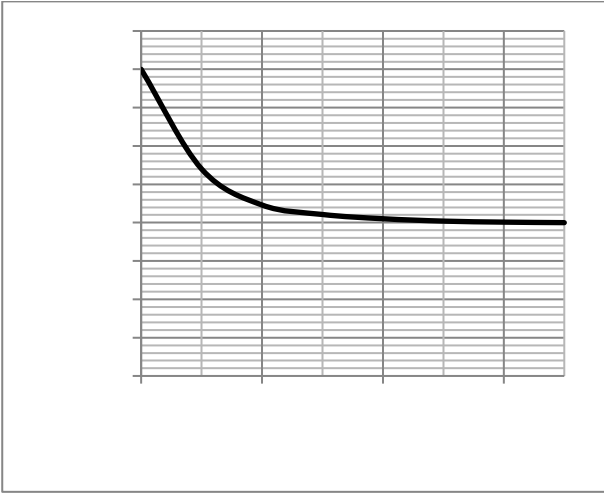


Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform

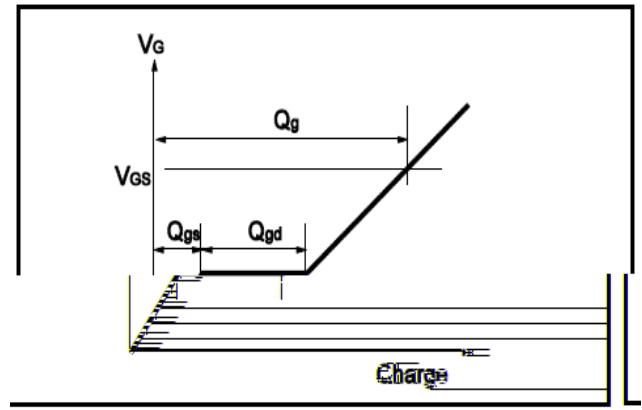
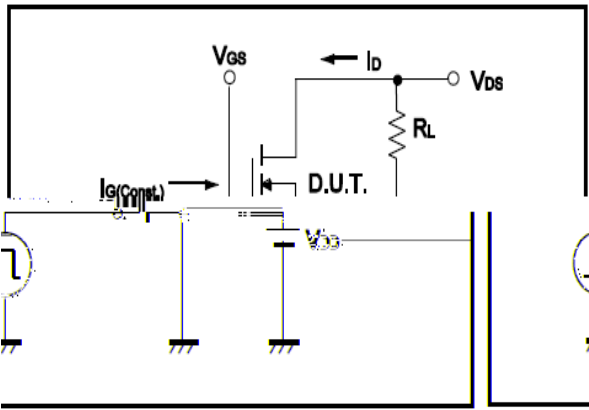
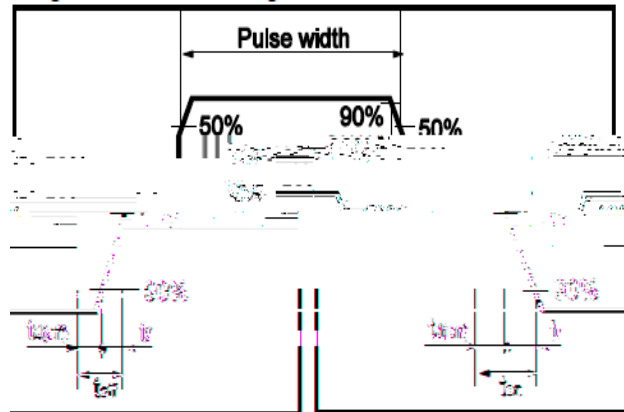
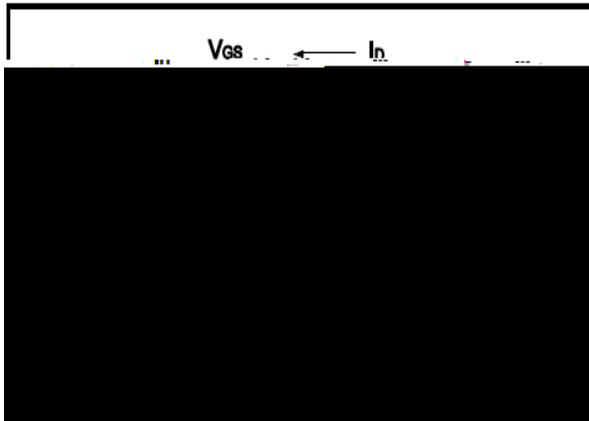


Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform





Dimensions(SOP8)

Unit: mm

